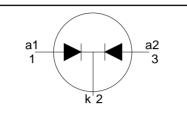
PBYR325CTD series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance



SYMBOL

QUICK REFERENCE DATA

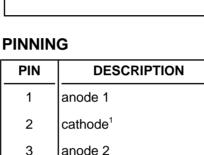
$$V_R = 20 \text{ V}/25 \text{ V}$$

 $I_{O(AV)} = 3 \text{ A}$
 $V_F \le 0.4 \text{ V}$

GENERAL DESCRIPTION

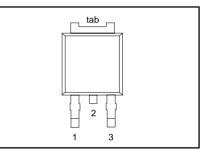
Dual schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR325CTD series is supplied in the SOT428 surface mounting package.



cathode

SOT428



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

tab

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
		PBYR3		20CTD	25CTD	
V _{RRM}	Peak repetitive reverse voltage		-	20	25	V
V _{RWM}	Working peak reverse voltage		-	20	25	V
V _R	Continuous reverse voltage	$T_{mb} \le 125 \ ^{\circ}C$	-	20	25	V
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; δ = 0.5; T _{mb} \leq 144 °C	-	3		A
I _{FRM}	Repetitive peak forward current per diode	square wave; δ = 0.5; T _{mb} \leq 144 °C	-	3		A
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; T _i = 125 °C prior to surge; with reapplied V _{RRM(max)}	-	55 60		A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{j max}	-	1		A
T _j	Operating junction temperature	Jinax	-	150		°C
T _{stg}	Storage temperature		- 65	175		°C

¹ it is not possible to make connection to pin 2 of the SOT428 package

PBYR325CTD series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb} R _{th j-a}	to mounting base	per diode both diodes pcb mounted, minimum footprint, FR4 board		- - 50	5 4 -	K/W K/W K/W

ELECTRICAL CHARACTERISTICS

All characteristics are per diode at $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	I _F = 1.5 A; T _i = 125°C	-	0.34	0.4	V
· ·		$I_{\rm F} = 3 \text{ A}; T_{\rm i} = 125 ^{\circ} \text{C}$	-	0.39	0.5	V
		$I_{\rm F} = 3 {\rm A}^{-1}$	-	0.47	0.6	V
I _R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	0.05	2	mA
		$V_{R} = V_{RWM}; T_{i} = 100^{\circ}C$	-	4	8	mA
C _d	Junction capacitance	$V_{R} = 5 \text{ V}; \text{ f} = 1 \text{ MHz}, \text{ T}_{j} = 25 ^{\circ}\text{C} \text{ to } 125 ^{\circ}\text{C}$	-	117	-	pF

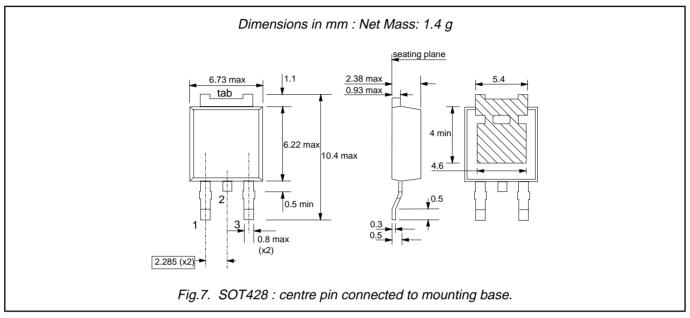
PBYR325CTD series

Rectifier diodes Schottky barrier

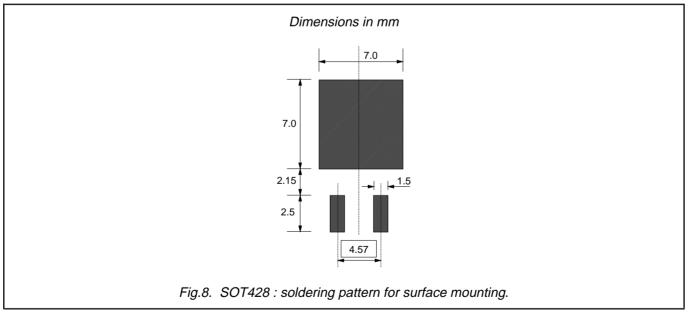
Tmb(max) / C 145 Forward dissipation, PF (W) Reverse current, IR (A) 100mA 1 Vo = 0.3 V Rs = 0.067 Ohms D = 1.0 -150 C 015 0.8 146 10mA 125 C 0.2 100 C 0.6 147 1mA 0 1 75 C 0.4 148 100uA 50 C D 0.2 _Tj = 25 C 149 10uA 150 0 1uA 0.5 1 1.5 2 2.5 0 10 25 5 20 15 Average forward current, IF(AV) (A) Reverse voltage, VR (V) Fig.1. Maximum forward dissipation per diode Fig.4. Typical reverse leakage current per diode; $\vec{P}_{F} = f(I_{F(AV)});$ square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$ $I_R = f(V_R)$; parameter T_i T<u>mb(max) / C</u>____146 Forward dissipation, PF (W) Junction capacitance, Cd (pF 1000 0.8 Vo = 0.3 V Rs = 0.067 ohms a = 1.5707 2.2 0.6 147 28 0.5 0.4 148 100 0.3 0.2 149 0.1 150 0 10 0 0.5 1 1.5 10 100 Average forward current, IF(AV) (A) Reverse voltage, VR (V) Fig.5. Typical junction capacitance per diode; $C_d = f(V_R); f = 1 \text{ MHz}; T_j = 25^{\circ}C \text{ to } 125^{\circ}C.$ Fig.2. Maximum forward dissipation per diode $P_F = f(I_{F(AV)})$; sinusoidal current waveform where $a = form factor = I_{F(RMS)} / I_{F(AV)}$. Transient thermal impedance, Zth j-mb (K/W) Forward current, IF (A) 10 6 Ti = 25 C Tj = 125 C 5 typ 1 0.1 З max 2 0.01 t_P D 1 . سند |---| T 0.001 └─ 1us 0 100us 1ms 10ms 100ms 1s 10us 10s 0.8 0 0.2 0.4 0.6 1 pulse width, tp (s) Forward voltage, VR (V) Typical and maximum forward characteristic Fig.6. Transient thermal impedance per diode; Fig.3. per diode $I_F = f(V_F)$; parameter T_i $Z_{th j-mb} = f(t_p).$

PBYR325CTD series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

- 1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
- 2. Epoxy meets UL94 V0 at 1/8".

PBYR325CTD series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	ninary specification This data sheet contains preliminary data; supplementary data may be published late			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				
Where application information is given, it is advisory and does not form part of the specification.				
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